

VOLTAGE 40 Volts **POWER** 200 mWatts

FEATURES

- Epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = 40V$
- Collector current $I_C = 200mA$
- In compliance with EU RoHS 2002/95/EC directives
- Transition Frequency $> 300MHz$ $f_T@I_C=10mA, V_{CE}=20V, f=100MHz$

MECHANICAL DATA

- Case: SOT-363, Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.006 gram
- Marking: S3A

SOT-363 Unit: inch (mm)

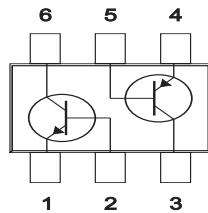
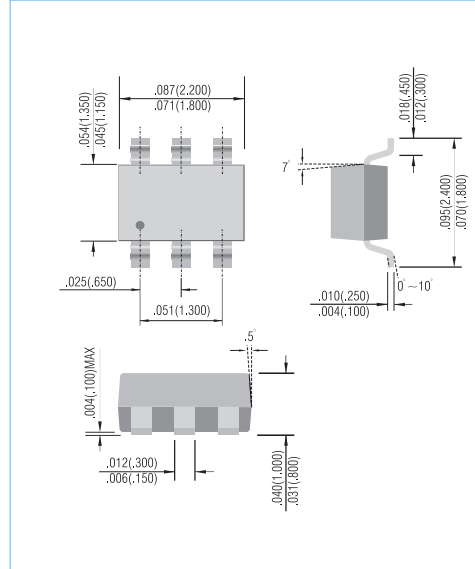


Fig.55

ABSOLUTE RATINGS

ABSOLUTE RATING		NPN 3904 Section	PNP 3906 Section	-
PARAMETER	Symbol	Value	Value	Units
Collector - Emitter Voltage	V_{CEO}	40	-40	V
Collector - Base Voltage	V_{CBO}	60	-40	V
Emitter - Base Voltage	V_{EBO}	6.0	-5.0	V
Collector Current - Continuous	I_C	200	-200	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	200	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}C/W$
Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$

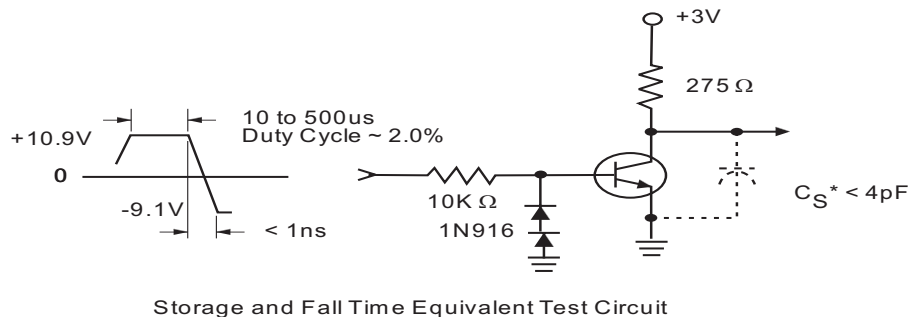
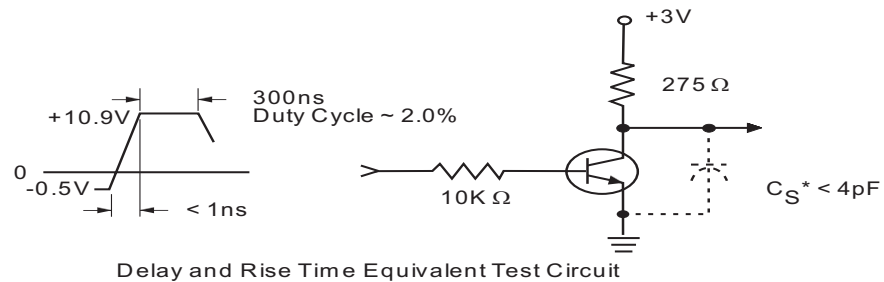
Note 1: Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.

ELECTRICAL CHARACTERISTICS NPN SECTION

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1.0mA, I_B=0$	40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6.0	-	-	V
Base Cutoff Current	I_{BI}	$V_{CE}=30V, V_{EB}=3.0V$	-	-	50	nA
Collector Cutoff Current	I_{CEX}	$V_{CE}=30V, V_{EB}=3.0V$	-	-	50	nA
DC Current Gain (Note 2)	h_{FE}	$I_C=0.1mA, V_{CE}=1.0V$ $I_C=1.0mA, V_{CE}=1.0V$ $I_C=10mA, V_{CE}=1.0V$ $I_C=50mA, V_{CE}=1.0V$ $I_C=100mA, V_{CE}=1.0V$	40 70 100 60 30	- - - - -	- - 300 - -	-
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C=10mA, I_B=1.0mA$ $I_C=50mA, I_B=5.0mA$	-	-	0.2 0.3	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C=10mA, I_B=1.0mA$ $I_C=50mA, I_B=5.0mA$	0.65 -	- -	0.85 0.95	V
Collector - Base Capacitance	C_{CBO}	$V_{CB}=5V, I_E=0, f=1MHz$	-	-	4.0	pF
Emitter - Base Capacitance	C_{EBO}	$V_{CB}=0.5V, I_C=0, f=1MHz$	-	-	8.0	pF
Delay Time	t_d	$V_{CC}=3V, V_{BE}=-0.5V,$ $I_C=10mA, I_B=1.0mA$	-	-	35	ns
Rise Time	t_r	$V_{CC}=3V, V_{BE}=-0.5V,$ $I_C=10mA, I_B=1.0mA$	-	-	35	ns
Storage Time	t_s	$V_{CC}=3V, I_C=10mA$ $I_{B1}=I_{B2}=1.0mA$	-	-	200	ns
Fall Time	t_f	$V_{CC}=3V, I_C=10mA$ $I_{B1}=I_{B2}=1.0mA$	-	-	50	ns

Note 2: Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.

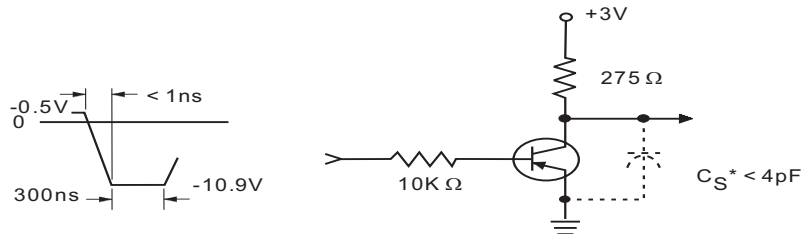
SWITCHING TIME EQUIVALENT TEST CIRCUITS



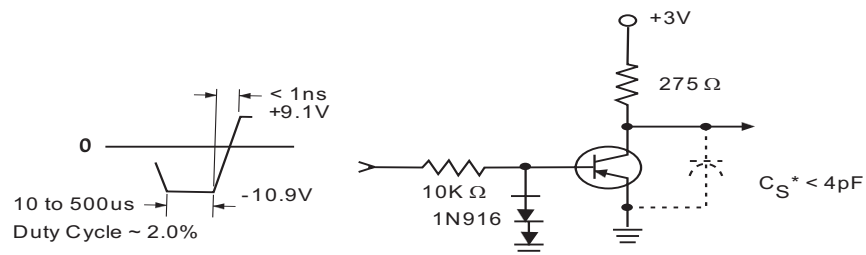
ELECTRICAL CHARACTERISTICS PNP SECTION

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1.0mA, I_B = 0$	-40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-40	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5.0	-	-	V
Base Cutoff Current	I_{BI}	$V_{CE} = -30V, V_{EB} = -3.0V$	-	-	-50	nA
Collector Cutoff Current	I_{CEX}	$V_{CE} = -30V, V_{EB} = -3.0V$	-	-	-50	nA
DC Current Gain (Note 2)	h_{FE}	$I_C = -0.1mA, V_{CE} = -1.0V$ $I_C = -1.0mA, V_{CE} = -1.0V$ $I_C = -10mA, V_{CE} = -1.0V$ $I_C = -50mA, V_{CE} = -1.0V$ $I_C = -100mA, V_{CE} = -1.0V$	60 80 100 60 30	- - - - -	- - 300 - -	-
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C = -10mA, I_B = -1.0mA$ $I_C = -50mA, I_B = -5.0mA$	-	-	-0.25 -0.4	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C = -10mA, I_B = -1.0mA$ $I_C = -50mA, I_B = -5.0mA$	-0.65 -	- -	-0.85 -0.95	V
Collector - Base Capacitance	C_{CBO}	$V_{CB} = -5V, I_E = 0, f = 1MHz$	-	-	4.0	pF
Emitter - Base Capacitance	C_{EBO}	$V_{CB} = -0.5V, I_C = 0, f = 1MHz$	-	-	10	pF
Delay Time	t_d	$V_{CC} = -3V, V_{BE} = -0.5V,$ $I_C = -10mA, I_B = -1.0mA$	-	-	35	ns
Rise Time	t_r	$V_{CC} = -3V, V_{BE} = -0.5V,$ $I_C = -10mA, I_B = -1.0mA$	-	-	35	ns
Storage Time	t_s	$V_{CC} = -3V, I_C = -10mA$ $I_{B1} = I_{B2} = -1.0mA$	-	-	225	ns
Fall Time	t_f	$V_{CC} = -3V, I_C = -10mA$ $I_{B1} = I_{B2} = 1.0mA$	-	-	75	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Delay and Rise Time Equivalent Test Circuit



Storage and Fall Time Equivalent Test Circuit

ELECTRICAL CHARACTERISTICS CURVE NPN SECTION

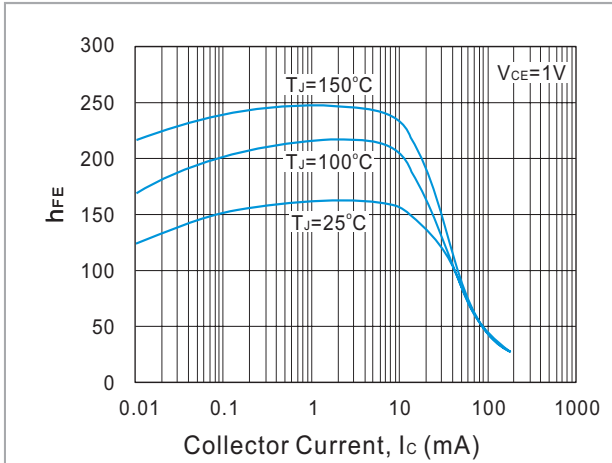


Fig. 1. Typical h_{FE} vs. Collector Current

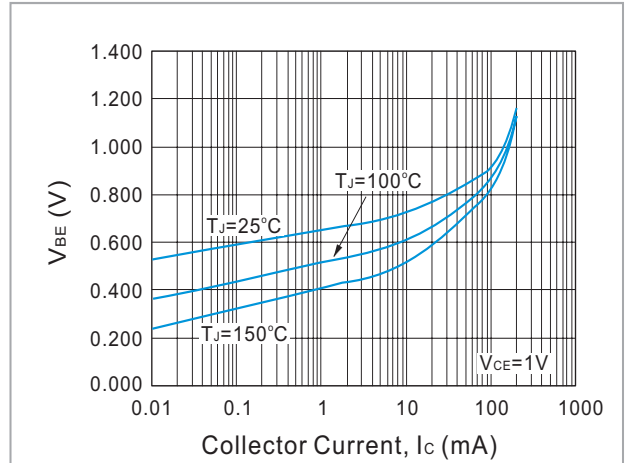


Fig. 2. Typical V_{BE} vs. Collector Current

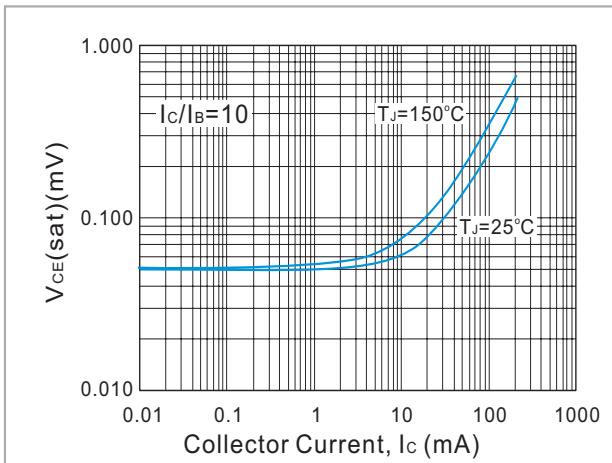


Fig. 3. Typical $V_{CE(sat)}$ vs. Collector Current

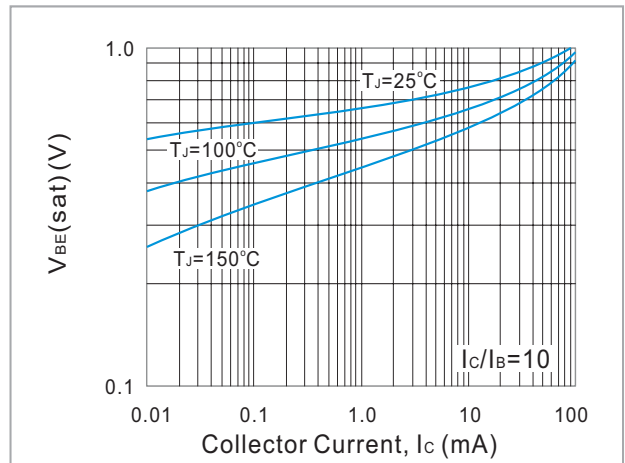


Fig. 4. Typical $V_{BE(sat)}$ vs. Collector Current

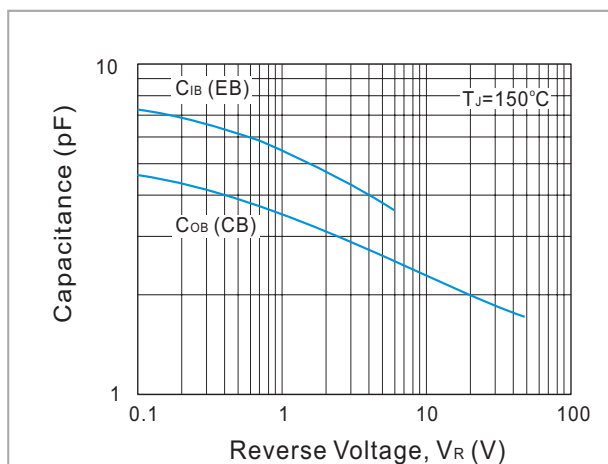


Fig. 5. Typical Capacitances vs. Reverse Voltage

ELECTRICAL CHARACTERISTICS CURVE PNP SECTION

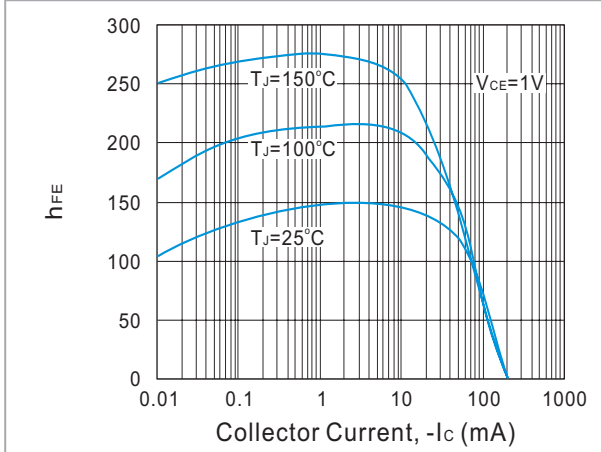


Fig. 1. Typical h_{FE} vs Collector Current

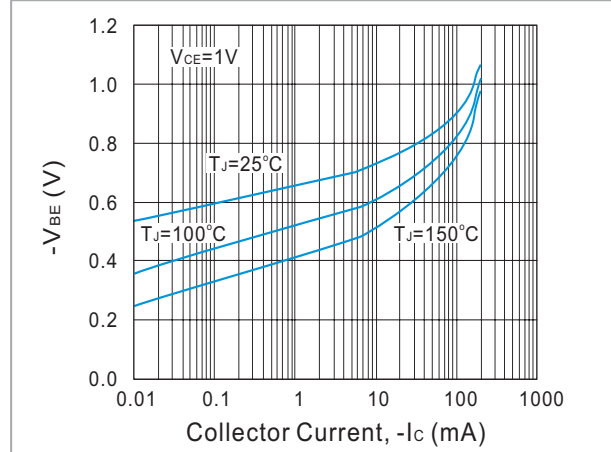


Fig. 2. Typical V_{BE} vs Collector Current

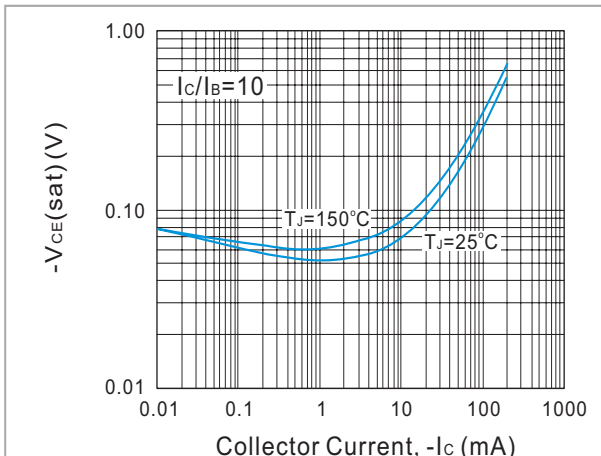


Fig. 3. Typical $V_{CE(sat)}$ vs Collector Current

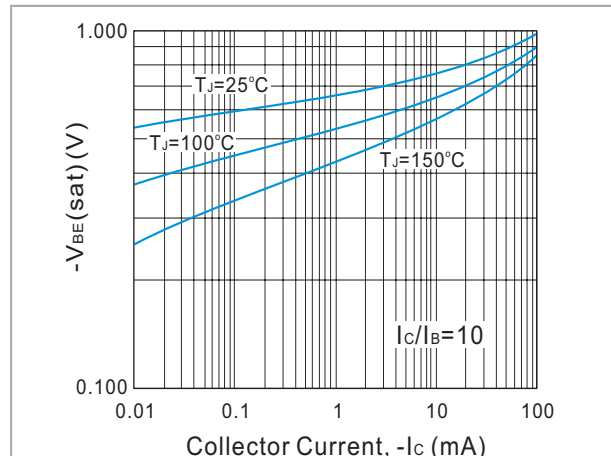


Fig. 4. Typical $V_{BE(sat)}$ vs Collector Current

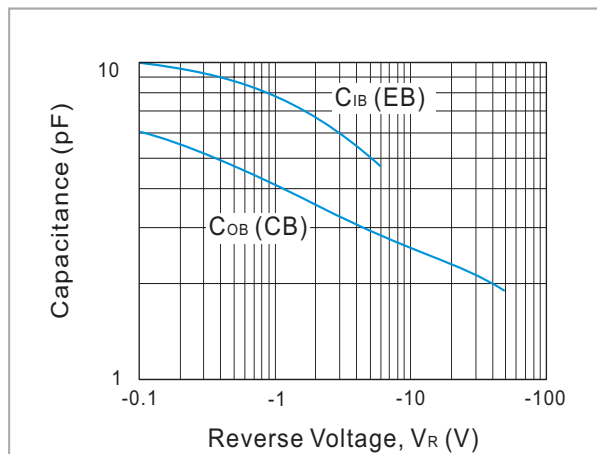
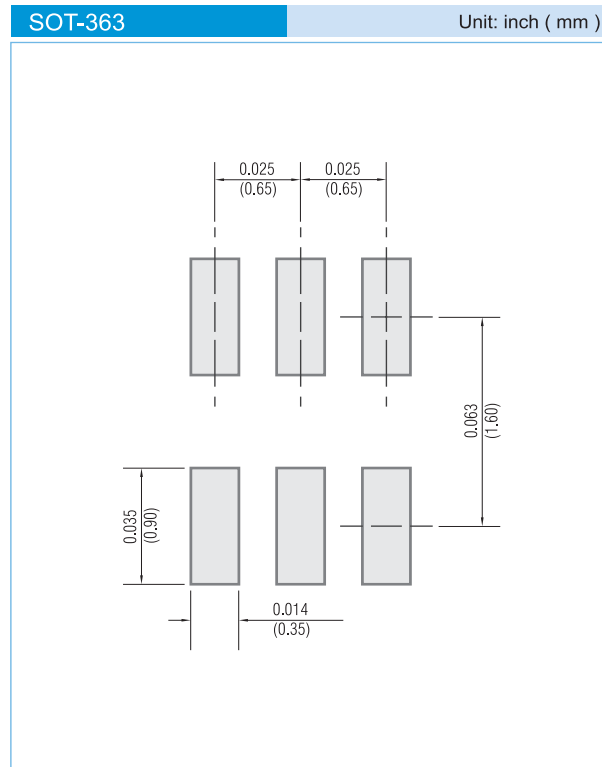


Fig. 5. Typical Capacitances vs Reverse Voltage

MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 10K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel